CLAIM AMENDMENTS

1.-8. (Cancelled)

9. (Original) An electrical device comprising:

electrical contact pads to receive a supply voltage;

a power bus electrically connected to the electrical contact pads; and

an interconnection circuit to, for each electrical contact pad, form a redundant connection between the bus and the electrical contact pad.

10. (Original) The electrical device of claim 9, wherein

the electrical device comprises a semiconductor device comprising having multiple process layers, and

the interconnection circuit is formed in the same process layer as the power bus.

11. (Original) The electrical device of claim 9, wherein

the electrical device comprises a semiconductor device comprising having multiple process layers, and

the interconnection circuit is formed in one of the process layers located between another one of the process layers in which the bus is formed and the electrical contacts.

12. (Original) The electrical device of claim 9, wherein the interconnection circuit comprises:

switches to selectively form the redundant connections.

13. (Original) The electrical device of claim 9, wherein the device comprises a microprocessor.

14.-19. (Cancelled)

20. (Original) A method usable with a semiconductor device, comprising:

electrical connecting external contacts of a semiconductor device to internal buses of the semiconductor device; and

establishing redundant connections between the buses and the external contacts.

21. (Original) The method of claim 20, further comprising:

forming the buses in a first process layer; and

forming the redundant connections in the same first process layer.

22. (Original) The method of claim 20, further comprising:

forming the buses in a first process layer; and

forming the redundant connections in a second process layer different from the first process layer.

23. (Original) The method of claim 20, further comprising:

forming a passivation layer;

providing contacts that are exposed for external connections with the semiconductor device on one side of the passivation layer; and

forming the redundant connections on said one side.

24. (Original) The method of claim 23, wherein the forming comprises:

depositing a metal layer on said one side; and

selectively etching the metal layer to form the redundant connections.